

# 2SD0875 (2SD875)

## Silicon NPN epitaxial planar type

For low-frequency power amplification  
Complementary to 2SB0767 (2SB767)

### ■ Features

- Large collector power dissipation  $P_C$
- High collector-emitter voltage (Base open)  $V_{CEO}$
- Mini power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter                             | Symbol    | Rating      | Unit             |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | $V_{CBO}$ | 80          | V                |
| Collector-emitter voltage (Base open) | $V_{CEO}$ | 80          | V                |
| Emitter-base voltage (Collector open) | $V_{EBO}$ | 5           | V                |
| Collector current                     | $I_C$     | 0.5         | A                |
| Peak collector current                | $I_{CP}$  | 1           | A                |
| Collector power dissipation *         | $P_C$     | 1           | W                |
| Junction temperature                  | $T_j$     | 150         | $^\circ\text{C}$ |
| Storage temperature                   | $T_{stg}$ | -55 to +150 | $^\circ\text{C}$ |

Note) \*: Printed circuit board: Copper foil area of  $1\text{ cm}^2$  or more, and the board thickness of 1.7 mm for the collector portion

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

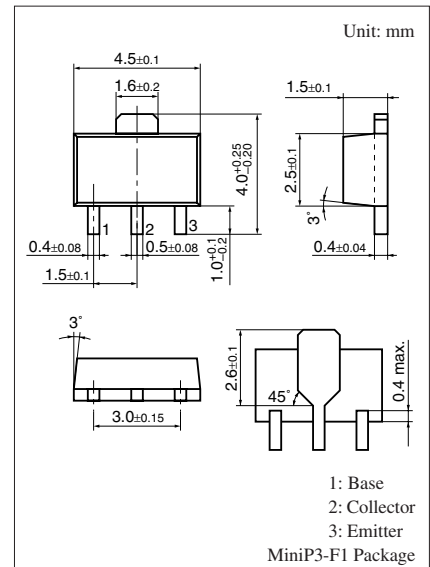
| Parameter   | Symbol        | Conditions   | Min | Typ  | Max | Unit          |
|---|---------------|--|-----|------|-----|---------------|
| Collector-base voltage (Emitter open)                               | $V_{CBO}$     | $I_C = 10\ \mu\text{A}, I_E = 0$                                   | 80  |      |     | V             |
| Collector-emitter voltage (Base open)                               | $V_{CEO}$     | $I_C = 100\ \mu\text{A}, I_B = 0$                                  | 80  |      |     | V             |
| Emitter-base voltage (Collector open)                               | $V_{EBO}$     | $I_E = 10\ \mu\text{A}, I_C = 0$                                   | 5   |      |     | V             |
| Collector-base cutoff current (Emitter open)                        | $I_{CBO}$     | $V_{CB} = 20\ \text{V}, I_E = 0$                                   |     |      | 0.1 | $\mu\text{A}$ |
| Forward current transfer ratio                                      | $h_{FE1}$ *   | $V_{CE} = 10\ \text{V}, I_C = 150\ \text{mA}$                      | 130 |      | 330 | —             |
|   | $h_{FE2}$     | $V_{CE} = 50\ \text{V}, I_C = 500\ \text{mA}$                      | 50  | 100  |     |               |
| Collector-emitter saturation voltage                                | $V_{CE(sat)}$ | $I_C = 300\ \text{mA}, I_B = 30\ \text{mA}$                        |     | 0.2  | 0.4 | V             |
| Base-emitter saturation voltage                                     | $V_{BE(sat)}$ | $I_C = 300\ \text{mA}, I_B = 30\ \text{mA}$                        |     | 0.85 | 1.2 | V             |
| Transition frequency  | $f_T$         | $V_{CB} = 10\ \text{V}, I_E = -50\ \text{mA}, f = 200\ \text{MHz}$ |     | 120  |     | MHz           |
| Collector output capacitance<br>(Common base, input open circuited) | $C_{ob}$      | $V_{CB} = 10\ \text{V}, I_E = 0, f = 1\ \text{MHz}$                |     | 11   | 20  | pF            |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

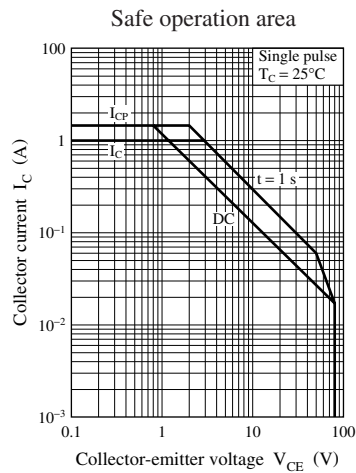
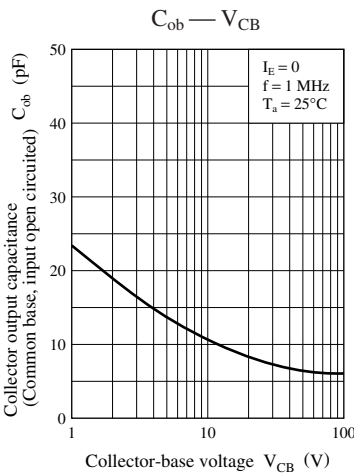
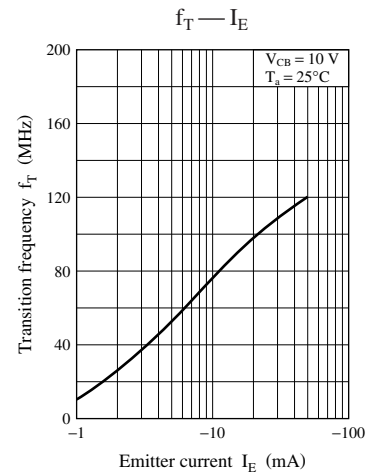
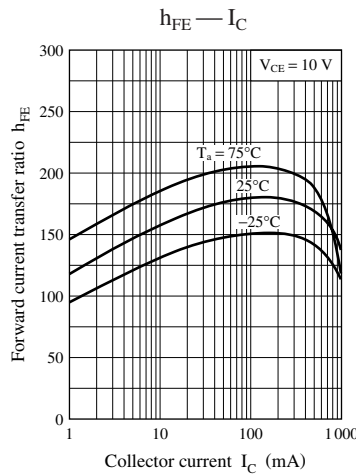
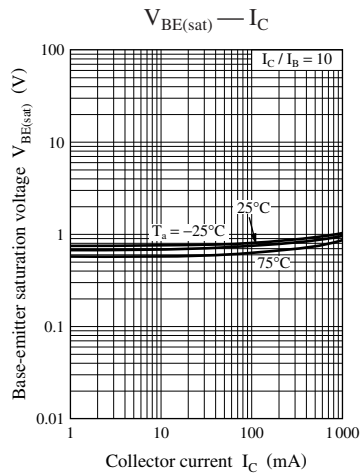
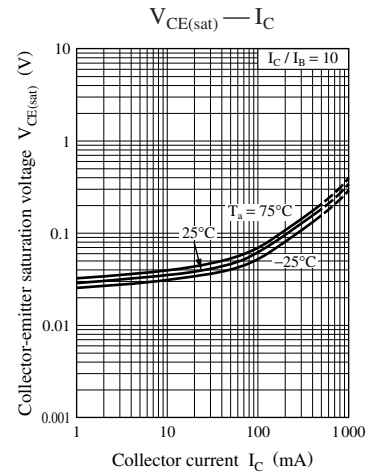
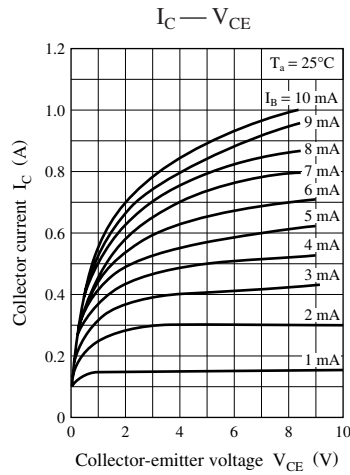
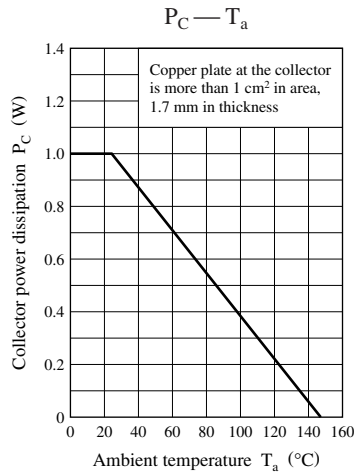
2. \*: Rank classification

| Rank      | R          | S          |
|-----------|------------|------------|
| $h_{FE1}$ | 130 to 220 | 185 to 330 |

Note) The part number in the parenthesis shows conventional part number.



Marking Symbol: X



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